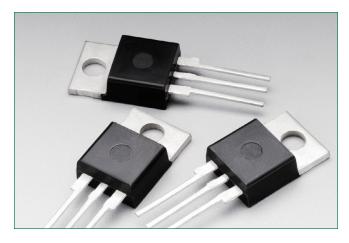
Through Hole Radial – 800V





## **Additional Information**







Accessories



Samples

## **Description**

The BTB08 is designed for high performance full-wave AC control applications where high noise immunity and high commutating di/dt are required.

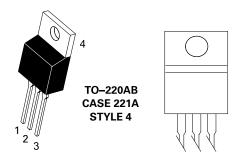
#### **Features**

- Blocking Voltage to 800 V
- On-State Current Rating of 8 Amperes RMS at 25°C
- Uniform Gate Trigger Currents in Three Quadrants
- High Immunity to dV/dt 2000 V/µs minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO-220AB Package
- High Commutating dl/dt 4 A/ms minimum at 125°C
- These are Pb-Free Devices

### **Functional Diagram**



### **Pin Out**





Through Hole Radial - 800V

### Maximum Ratings (TJ = 25°C unless otherwise noted)

Rating		Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, $T_J = -40^{\circ}$ to 125°C)	BTB08-600BW3G BTB08-800BW3G	V <sub>DRM</sub> , V <sub>RRM</sub>	600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_c = 80$	0°C)	I <sub>T (RMS)</sub>	18	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, $T_c$ = 25°C)		I <sub>TSM</sub>	90	А
Circuit Fusing Consideration (t = 10 ms)		l²t	36	A²sec
Non–Repetitive Surge Peak Off–State Voltage ( $T_J = 25^{\circ}$ C, t = 10 ms)	$V_{\rm DSM}/V_{\rm RSM}$	V <sub>DSM</sub> /V <sub>RSM</sub> +100	V	
Peak Gate Current ( $T_J = 125$ °C, $t = 20$ ms)	I <sub>GM</sub>	4.0	W	
Peak Gate Power (Pulse Width $\leq$ 1.0 $\mu$ s, $T_{c}$ = 80°C)	P <sub>GM</sub>	20	W	
Average Gate Power (T <sub>J</sub> = 125°C)	$P_{G(AV)}$	1.0	W	
Operating Junction Temperature Range	T <sub>J</sub>	-40 to +125	°C	
Storage Temperature Range	$T_{stg}$	-40 to +150	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### **Thermal Characteristics**

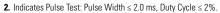
Rating	Symbol	Value	Unit	
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>eJC</sub> R <sub>eJA</sub>	2.5 60	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		$T_{\scriptscriptstyleL}$	260	°C

# **Electrical Characteristics - OFF** (TJ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T <sub>1</sub> = 25°C	I <sub>DRM</sub> ,	-	-	0.005	mΛ
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$	$T_{J}^{3} = 125^{\circ}C$	I	-	-	1.0	mA

# **Electrical Characteristics - ON** $(TJ = 25^{\circ}C)$ unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Forward On-State Voltage (Note 2) ( $I_{TM} = \pm 11$ A Peak)		$V_{TM}$	-	-	1.55	V
	MT2(+), G(+)		2.5	_	50	mA
Gate Trigger Current (Continuous dc) $(V_D = 12 \text{ V}, R_L = 30 \Omega)$	MT2(+), G(-)	l <sub>gt</sub>	2.5	_	50	
	MT2(-), G(-)		2.5	_	50	
Holding Current $(V_D = 12 \text{ V}, \text{ Gate Open, Initiating Current} = \pm 100 \text{ mA})$		I <sub>H</sub>	-	_	50	mA
	MT2(+), G(+)		-	_	70	mA
Latching Current ( $V_D = 24 \text{ V}$ , $I_G = 60 \text{ mA}$ )	MT2(+), G(-)	I <sub>L</sub>	_	_	90	
	MT2(-), G(-)		_	_	70	
	MT2(+), G(+)		0.5	_	1.7	
Gate Trigger Voltage ( $V_D = 12 \text{ V}, R_1 = 30 \Omega$ )	MT2(+), G(-)	$V_{GT}$	0.5	_	1.1	V
	MT2(-), G(-)	G.	0.5	_	1.1	
	MT2(+), G(+)		0.2	_	_	
Gate Non-Trigger Voltage (T <sub>J</sub> = 125°C)	MT2(+), G(-)	$V_{gd}$	0.2	_	_	V
- -	MT2(-), G(-)	35	0.2	_	_	





<sup>1.</sup> V<sub>cott</sub> and V<sub>cott</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Through Hole Radial – 800V

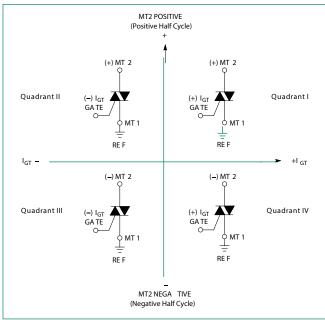
## **Dynamic Characteristics**

Characteristic	Symbol	Min	Тур	Max	Unit
Rate of Change of Commutating Current, See Figure 10. (Gate Open, $T_J = 125^{\circ}$ C, No Snubber)	(dl/dt)c	4.0	-	-	A/ms
Critical Rate of Rise of On–State Current ( $T_J = 125^{\circ}\text{C}$ , $f = 120$ Hz, $I_G = 2 \times I_{GT}$ , tr $\leq 100$ ns)	dl/dt	_	_	50	A/µs
Critical Rate of Rise of Off-State Voltage $(V_D = 0.66 \times V_{DRM'}, Exponential Waveform, Gate Open, T_J = 125°C)$	dV/dt	2000	_	_	V/µs

## **Voltage Current Characteristic of SCR**

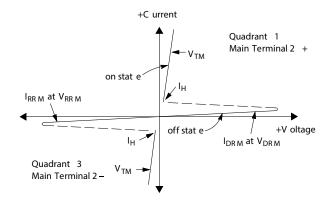
Symbol	Parameter
V <sub>DRM</sub>	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
$V_{TM}$	Maximum On State Voltage
I <sub>H</sub>	Holding Current

### **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.

With in –phase signals (using standard AC lines) quadrants I and III are used



Through Hole Radial – 800V

**Figure 1. RMS Current Derating** 

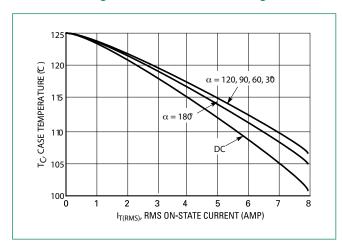


Figure 3. On-State Characteristics

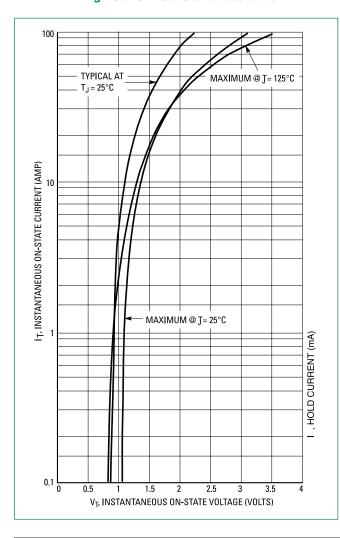
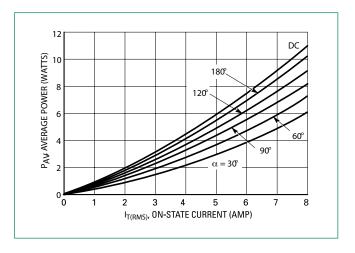


Figure 2. On-State Power Dissipation



**Figure 4. Thermal Response** 

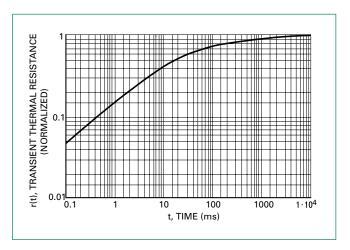
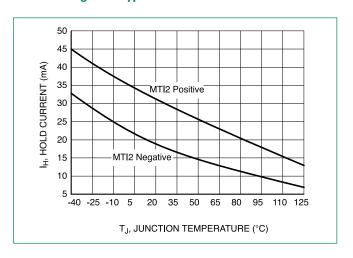


Figure 5. Typical Hold Current Variation





Through Hole Radial - 800V

**Figure 6. Typical Gate Trigger Current Variation** 

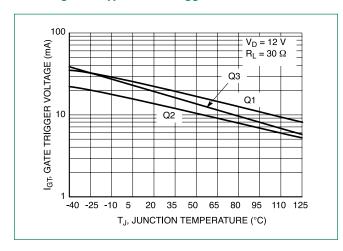


Figure 8. Critical Rate of Rise of Off-State Voltage (Exponential Waveform)

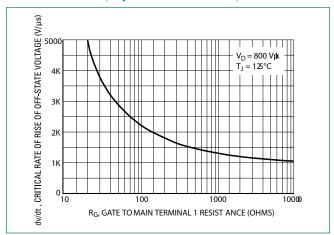


Figure 7. Typical Gate Trigger Voltage Variation

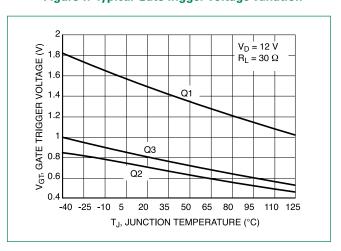
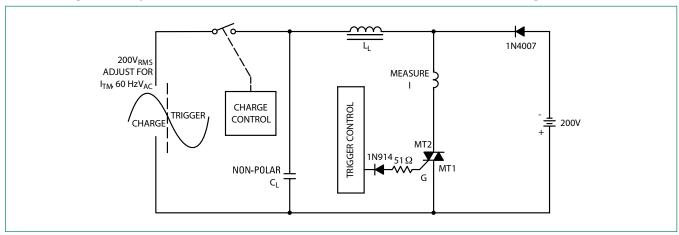


Figure 9. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)

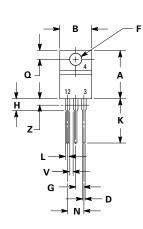


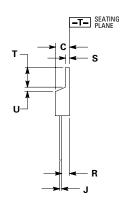
Note: Component values are for verification of rated (di/dt)c. See AN1048 for additional information



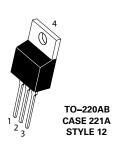
Through Hole Radial – 800V

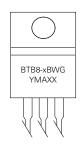
### **Dimensions**





### **Part Marking System**





x =6 or 8 Y =V22

Y = Year
M = Month
A = Assembly Site
XX = Lot Serial Code

G =Pb-Free Package

**Pin Assignment** 

TO-220AB

(Pb-Free)

Main Terminal 1 Main Terminal 2

> Shipping 1000 Units / Box

1000 Units / Box

D:	Inc	hes	Millimeters		
Dim	Min	Max	Min	Max	
Α	0.590	0.620	14.99	15.75	
В	0.380	0.420	9.65	10.67	
С	0.178	0.188	4.52	4.78	
D	0.025	0.035	0.64	0.89	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.41	2.67	
Н	0.110	0.130	2.79	3.30	
J	0.018	0.024	0.46	0.61	
K	0.540	0.575	13.72	14.61	
L	0.060	0.075	1.52	1.91	
N	0.195	0.205	4.95	5.21	
Q	0.105	0.115	2.67	2.92	
R	0.085	0.095	2.16	2.41	
S	0.045	0.060	1.14	1.52	
T	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

3	Ga	ite		
4	No Connection			
Ordering Infor	mation			
Device	Package	:		
BTB08-600BW3G	TO-220AB (Pb-Free)	100		

BTB08-800BW3G



<sup>1.</sup> Dimensioning and tolerancing per ansi y14.5m, 1982.

Controlling dimension: inch.
 Dimension z defines a zone where all body and lead irregularities are allowed.